

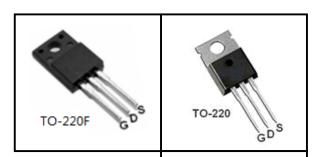
## **600V N-Channel MOSFET**

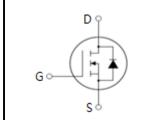
#### **FEATURES**

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

#### **APPLICATIONS**

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)





Device Marking and Package Information				
Device Package		Marking		
CS16N60F	TO-220F	CS16N60F		
CS16N60P	TO-220	CS16N60P		

<b>Absolute Maximum Ratings</b> $T_C = 25^{\circ}C$ , unless otherwise noted					
Barranadan	Symbol	Va	11.24		
Parameter		TO-220F	TO-220	Unit	
Drain-Source Voltage (V <sub>GS</sub> = 0V)	$V_{\rm DSS}$	600		V	
Continuous Drain Current	I <sub>D</sub>	16		А	
Pulsed Drain Current (note1)	I <sub>DM</sub>	64		Α	
Gate-Source Voltage	$V_{GSS}$	±30		\ \	
Single Pulse Avalanche Energy (note2)	E <sub>AS</sub>	376		mJ	
Avalanche Current (note1)	I <sub>AS</sub>	8.7		А	
Repetitive Avalanche Energy (note1)	E <sub>AR</sub>	225		mJ	
Power Dissipation (T <sub>C</sub> = 25°C)	P <sub>D</sub>	63.7	104	W	
Operating Junction and Storage Temperature Range	$T_J,T_stg$	-55~+150		°C	

Thermal Resistance					
Barranta	Symbol	Va			
Parameter		TO-220F	TO-220	Unit	
Thermal Resistance, Junction-to-Case	R <sub>thJC</sub>	1.96	1.2	12/\\	
Thermal Resistance, Junction-to-Ambient	R <sub>thJA</sub>	62.5	60	K/W	



<b>Specifications</b> $T_J = 25^{\circ}C$ , unless otherwise noted							
Parameter	Symbol	Test Conditions	Value			Unit	
raiametei	Symbol	rest conditions	Min.	Тур.	Max.	Oilit	
Static							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	600			V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 600V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μA	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{GS} = \pm 30V$			±100	nA	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		4.0	V	
Drain-Source On-Resistance (Note3)	R <sub>DS(on)</sub>	$V_{GS} = 10V, I_D = 8.0A$		0.4	0.48	Ω	
Dynamic							
Input Capacitance	C <sub>iss</sub>	V 0V		2006		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0MHz$		214			
Reverse Transfer Capacitance	C <sub>rss</sub>			30			
Total Gate Charge	$Q_g$	$V_{DD} = 480V, I_{D} = 16A,$ $V_{GS} = 10V$		62		nC	
Gate-Source Charge	$Q_{gs}$			10			
Gate-Drain Charge	$Q_{gd}$			29			
Turn-on Delay Time	t <sub>d(on)</sub>	$V_{DD} = 300V, I_{D} = 16A,$ $R_{G} = 25 \Omega$		50		ns	
Turn-on Rise Time	t <sub>r</sub>			43			
Turn-off Delay Time	t <sub>d(off)</sub>			243			
Turn-off Fall Time	t <sub>f</sub>			70			
Drain-Source Body Diode Character	istics						
Continuous Body Diode Current	I <sub>S</sub>				16	А	
Pulsed Diode Forward Current	I <sub>SM</sub>	T <sub>C</sub> = 25 °C			64		
Body Diode Voltage	V <sub>SD</sub>	$T_J = 25^{\circ}C$ , $I_{SD} = 8A$ , $V_{GS} = 0V$			1.4	V	
Reverse Recovery Time	t <sub>rr</sub>	$V_{GS} = 0V, I_{S} = 16A,$		620		ns	
Reverse Recovery Charge	Q <sub>rr</sub>	di <sub>F</sub> /dt =100A /µs		3.84		μC	

## Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L = 10.0mH,  $V_{DD}$  = 50V,  $R_G$  = 25  $\Omega$ , Starting  $T_J$  = 25  $^{\circ}C$
- 3. Pulse Test: Pulse width  $\leq 300 \mu s$ , Duty Cycle  $\leq 1\%$

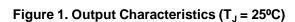


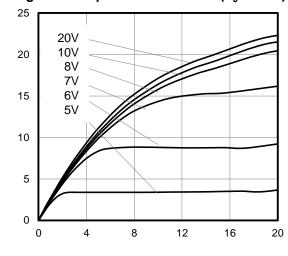
I<sub>D</sub>, Drain Current (A)

ID, Drain Current (A)

I<sub>D</sub>, Drain Current (A)

## **Typical Characteristics** $T_J = 25^{\circ}\text{C}$ , unless otherwise noted





 $V_{DS}$ , Drain-to-Source Voltage (V)

Figure 3. Drain Current vs. Temperature

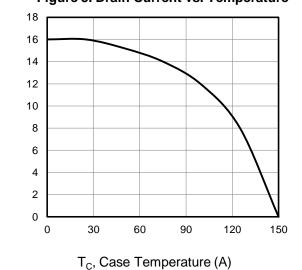


Figure 5. Transfer Characteristics

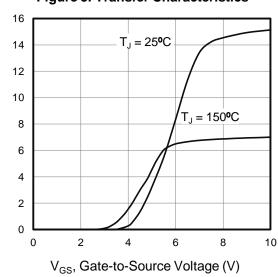
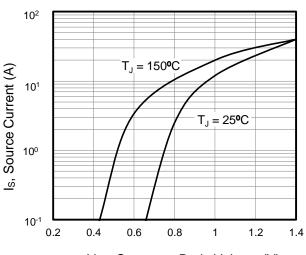
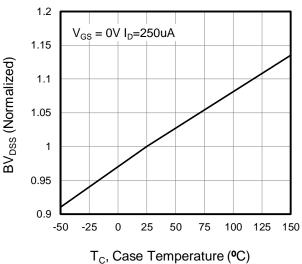


Figure 2. Body Diode Forward Voltage



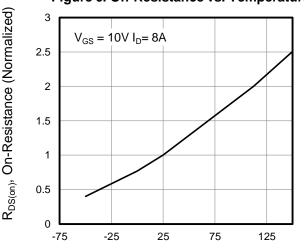
V<sub>SD</sub>, Source-to-Drain Voltage (V)

Figure 4.  $BV_{DSS}$  Variation vs. Temperature



C/ 1 ( /

Figure 6. On-Resistance vs. Temperature



T<sub>J</sub>, Junction Temperature (°C)



## **Typical Characteristics** $T_J = 25^{\circ}\text{C}$ , unless otherwise noted

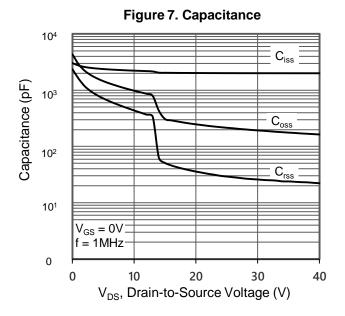


Figure 9. Transient Thermal Impedance
TO-220F

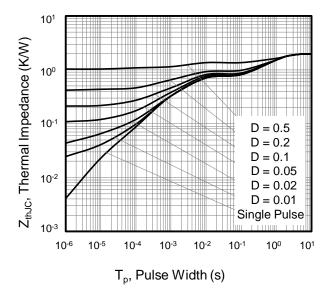


Figure 8. Gate Charge

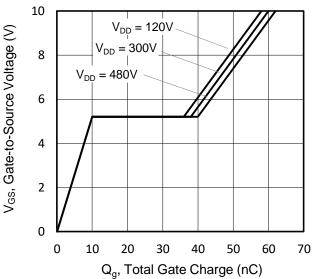


Figure 10. Transient Thermal Impedance TO-220

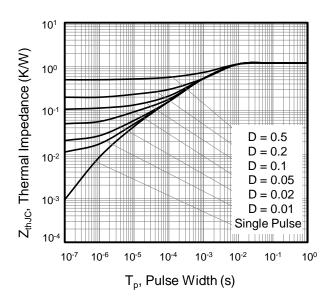




Figure A: Gate Charge Test Circuit and Waveform

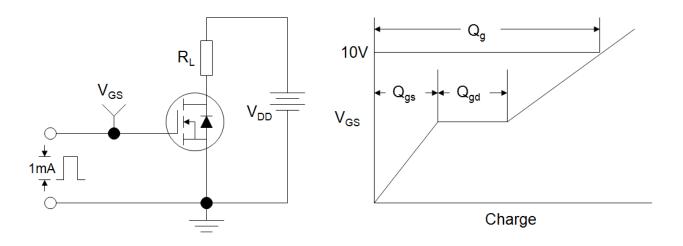


Figure B: Resistive Switching Test Circuit and Waveform

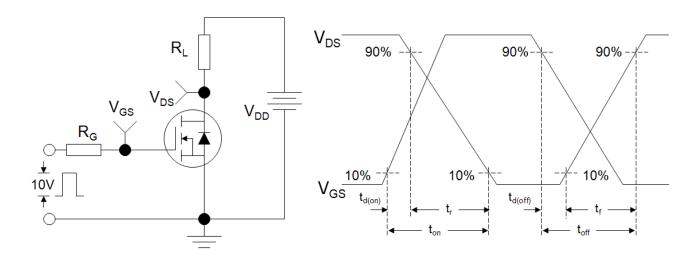
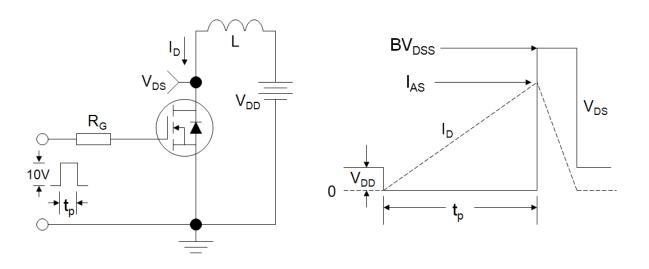
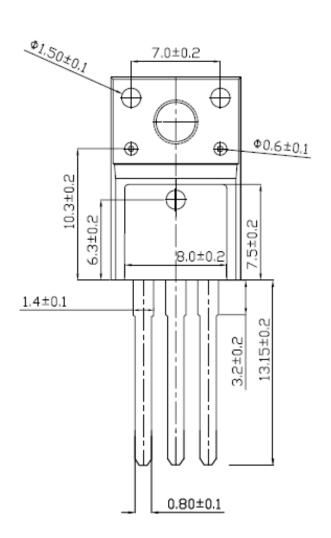


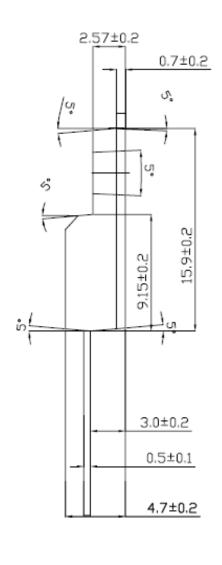
Figure C: Unclamped Inductive Switching Test Circuit and Waveform





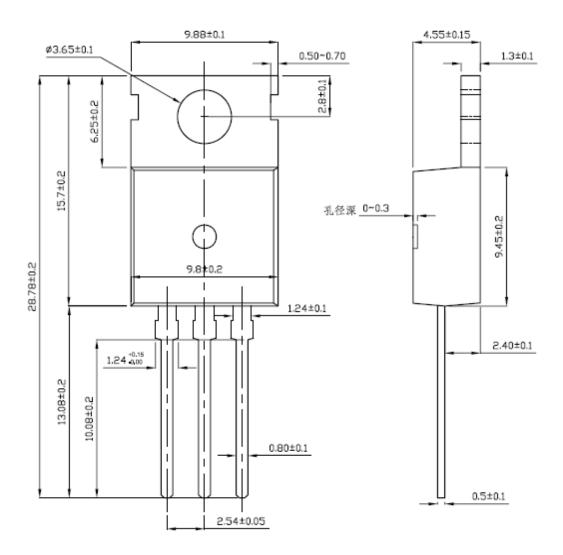
# **TO-220F**







# **TO-220**





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